Central™
Semiconductor Corp.

PROCESS CPS090

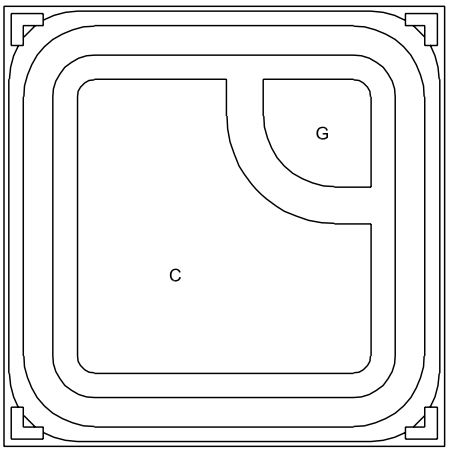
Silicon Controlled Rectifier

8.0 Amp Sensitive Gate SCR Chip

PROCESS DETAILS

Process	Glass Passivated Mesa
Die Size	90 x 90 MILS
Die Thickness	8.7 MILS
Cathode Bonding Pad Area	60 x 30 MILS
Gate Bonding Pad Area	22 x 22 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

GEOMETRY



BACKSIDE ANODE R0

GROSS DIER PER 4 INCH WAFER

1,310

PRINCIPAL DEVICE TYPES

CS220-8M Series
CSD-8M Series
CSDD-8M Series

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